

1. Record Nr.	UNINA9910876805703321
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Titolo	Latchup // Steven H. Voldman
Pubbl/distr/stampa	Chichester, West Sussex, England ; ; Hoboken, NJ, : John Wiley, c2007
ISBN	1-281-31816-7 9786611318161 0-470-51617-8 0-470-51616-X
Descrizione fisica	1 online resource (474 p.)
Disciplina	621.3815/2
Soggetti	Metal oxide semiconductors, Complementary - Defects Metal oxide semiconductors, Complementary - Reliability
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Latchup; Contents; About the Author; Preface; Acknowledgements; 1 CMOS Latchup; 1.1 CMOS LATCHUP; 1.1.1 CMOS Latchup-What is Latchup?; 1.1.2 CMOS Latchup-Why is Latchup Still an Issue ?; 1.1.3 Early CMOS Latchup History; 1.2 FUNDAMENTAL CONCEPTS OF LATCHUP DESIGN PRACTICE; 1.3 BUILDING A CMOS LATCHUP STRATEGY; 1.3.1 Building a CMOS Business Strategy - 18 Steps in Building a CMOS Latchup Business Strategy; 1.3.2 Building a CMOS Latchup Technology Strategy - 18 Steps in Building a CMOS Latchup Technology Strategy; 1.4 CMOS LATCHUP TECHNOLOGY MIGRATION STRATEGY 1.5 KEY METRICS OF LATCHUP DESIGN PRACTICE 1.6 CMOS LATCHUP TECHNOLOGY TRENDS AND SCALING; 1.7 KEY DEVELOPMENTS; 1.7.1 Key Innovations; 1.7.2 Key Contributions; 1.7.3 Key Patents; 1.8 LATCHUP FAILURE MECHANISMS; 1.9 CMOS LATCHUP EVENTS; 1.9.1 Power-Up Sequence Initiated Latchup; 1.9.2 Input Pin Overshoot and Power-Up Sequence Initiated Latchup; 1.9.3 Input Pin Undershoot and Power-Up Sequence Initiated Latchup; 1.9.4 Multiple Power Supply Power-Up Sequence Initiated Latchup; 1.9.5 Power Supply Overshoot Initiated Latchup; 1.9.6 Power Supply Undershoot Initiated Latchup 1.9.7 Power Supply (Ground Rail) Undershoot Initiated Latchup 1.10

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Interest in latchup is being renewed with the evolution of complimentary metal-oxide semiconductor (CMOS) technology, metal-oxide-semiconductor field-effect transistor (MOSFET) scaling, and high-level system-on-chip (SOC) integration. Clear methodologies that grant protection from latchup, with insight into the physics, technology and circuit issues involved, are in increasing demand. This book describes CMOS and BiCMOS semiconductor technology and their sensitivity to present day latchup phenomena, from basic over-voltage and over-current conditions, single event latchup (SEL) and cabl
